## **Examples of semiconductor lattices**

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Both group IV semiconductors, **germanium or Ge** and **silicon or Si, have** unit cube/cell(s) as shown below. They consist of two sublattices, each face centered cubic (fcc) that overlap in a structure called a <u>diamond lattice</u>.

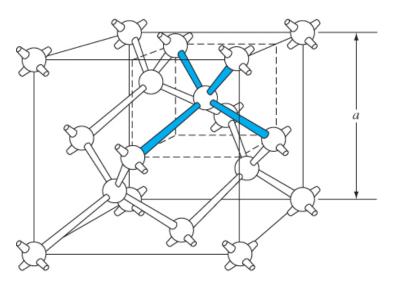
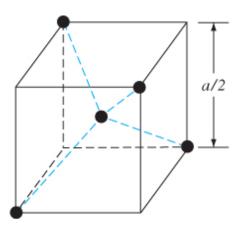


Figure 1.11 | The diamond structure.



**Figure 1.12** | The tetrahedral structure of closest neighbors in the diamond lattice.

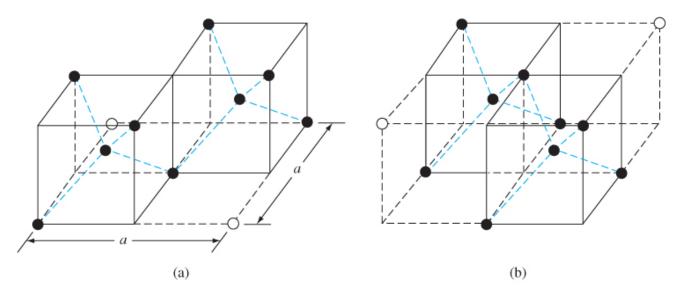
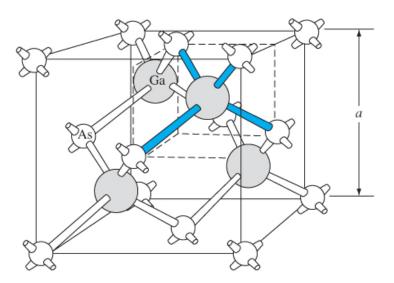


Figure 1.13 | Portions of the diamond lattice: (a) bottom half and (b) top half.

A gallium arsenide or GaAs unit cube/cell is shown below. It consists of two sublattices, each face centered cubic (fcc) and offset with respect to each other by half the diagonal of the fcc cube, a crystal configuration known as <u>cubic</u> <u>sphalerite/sphalerite</u> or <u>zinc blende/zincblende</u>. The key difference from the diamond lattice is that there are two different elements involved.



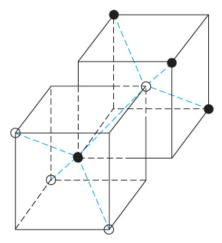


Figure 1.14 | The zincblende (sphalerite) lattice of GaAs.

**Figure 1.15** | The tetrahedral structure of closest neighbors in the zincblende lattice.